

### Internally Matched Power GaAs FETs (C-Band)

#### Features

- High power
  - $P_{1dB} = 42.5$  dBm at 3.7 GHz to 4.2 GHz
- High gain
  - $G_{1dB} = 9.5$  dB at 3.7 GHz to 4.2 GHz
- Broad band internally matched
- Hermetically sealed package

#### RF Performance Specifications ( $T_a = 25^\circ \text{C}$ )

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	$P_{1dB}$	$V_{DS} = 10V$ $f = 3.7 \sim 4.2 \text{ GHz}$	dBm	41.5	42.5	–
Power Gain at 1dB Compression Point	$G_{1dB}$		dB	8.5	9.5	–
Drain Current	$I_{DS}$		A	–	4.8	5.5
Power Added Efficiency	$\eta_{add}$		%	–	33	–
Channel-Temperature Rise	$\Delta T_{ch}$	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	$^\circ\text{C}$	–	–	80

#### Electrical Characteristics ( $T_a = 25^\circ \text{C}$ )

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 6.0 \text{ A}$	mS	–	3600	–
Pinch-off Voltage	$V_{GSoff}$	$V_{DS} = 3V$ $I_{DS} = 80\text{mA}$	V	-2	-3.5	-5
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	11.6	15.0
Gate to Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -240 \mu\text{A}$	V	-5	–	–
Thermal Resistance	$R_{th(c-c)}$	Channel to case	$^\circ\text{C/W}$	–	1.4	1.8

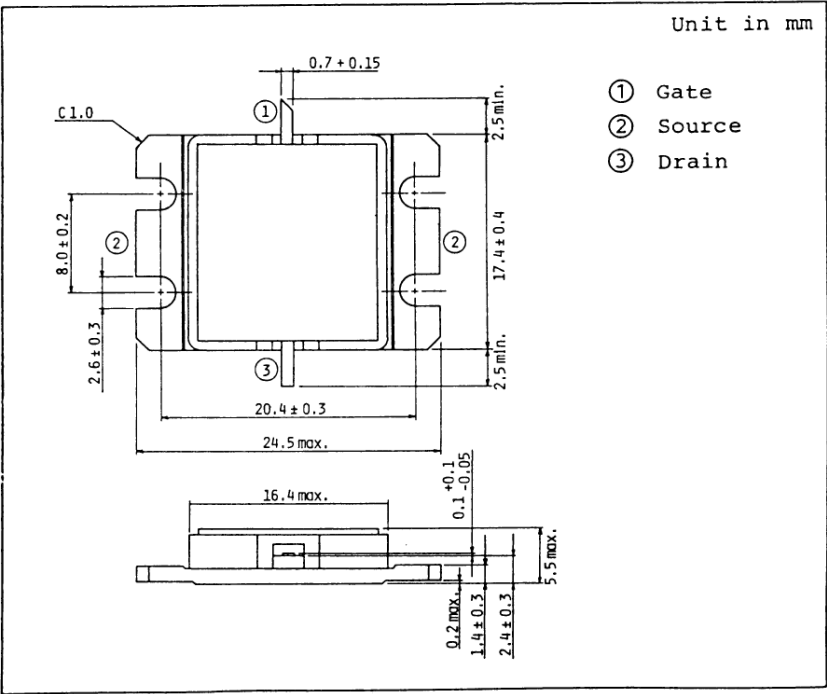
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Absolute Maximum Ratings (T<sub>a</sub> = 25° C)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V <sub>DS</sub>	V	15
Gate Source Voltage	V <sub>GS</sub>	V	-5
Drain Current	I <sub>D</sub>	A	16
Total Power Dissipation (T <sub>c</sub> = 25°C)	P <sub>T</sub>	W	70
Channel Temperature	T <sub>ch</sub>	°C	175
Storage Temperature	T <sub>stg</sub>	°C	-65~175

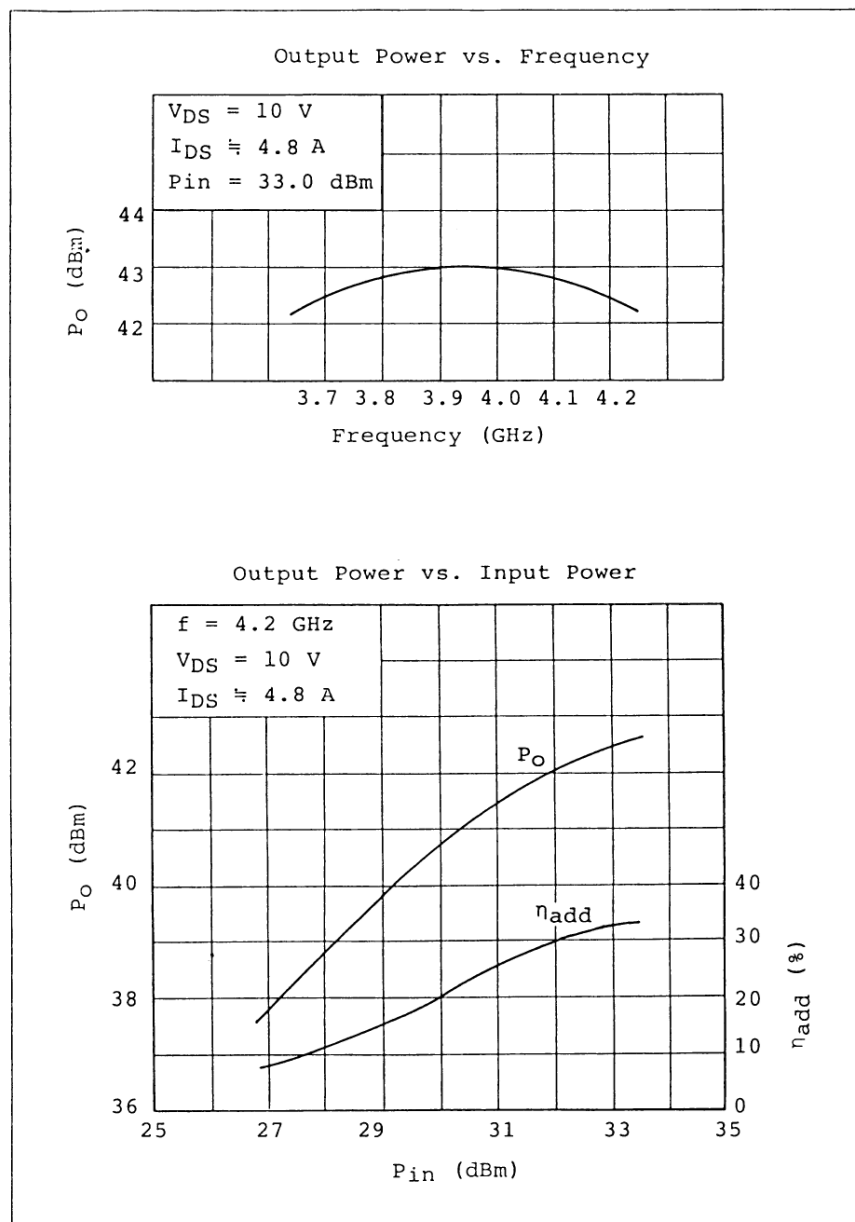
Package Outline (2-16G1B)



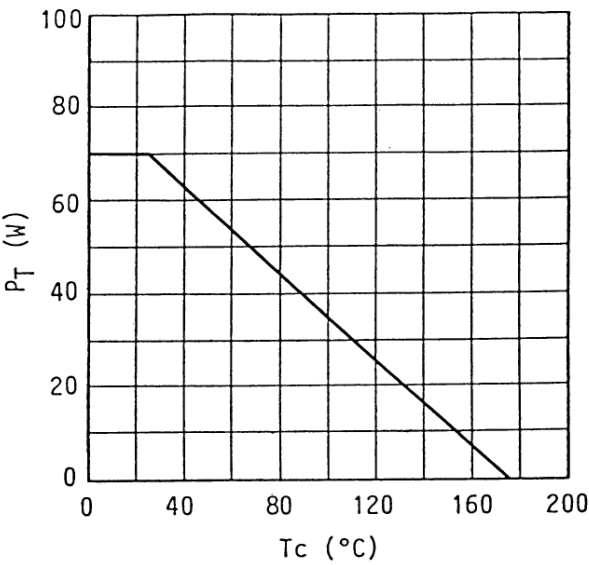
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

## RF Performances



Power Dissipation vs. Case Temperature



TPM3742-16 S-Parameters  
(MAGN. and ANGLES)

$$V_{DS} = 10 \text{ V}, I_{DS} = 4.0 \text{ A}$$

